

PDFN5060-8 N Channel Enhancement 沟道增强型 MOS Field Effect Transistor 场效应管

■Features 特点

Low on-resistance 低导通电阻

$R_{DS(ON)}=6.8m\Omega(\text{Type})@V_{GS}=10V$

$R_{DS(ON)}=8.5m\Omega(\text{Type})@V_{GS}=4.5V$

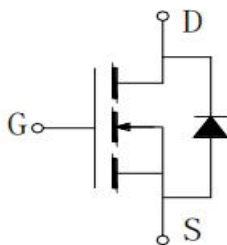
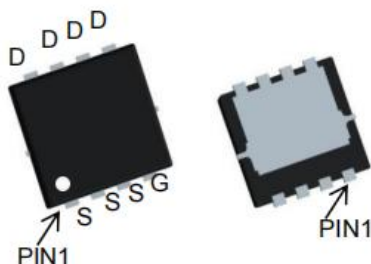
SGT Technology 屏蔽栅技术

Excellent QG x RDS(on) product(FOM)

■Applications 应用

Switch Application System 开关系统

■Internal Schematic Diagram 内部结构



■Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Drain-Source Voltage 漏极-源极电压	BV_{DSS}	100	V
Gate- Source Voltage 栅极-源极电压	V_{GS}	± 20	V
Drain Current (continuous)漏极电流-连续	I_D (at $T_C = 25^\circ\text{C}$ at $T_A = 25^\circ\text{C}$)	78 17	A
Drain Current (pulsed)漏极电流-脉冲	$I_{DM}(\text{at } T_C = 25^\circ\text{C})$	272	A
Total Device Dissipation 总耗散功率	$P_{TOT}(\text{at } T_C = 25^\circ\text{C}$ at $T_A = 25^\circ\text{C})$	57 4.2	W
Avalanche Energy(Single Pulse)雪崩能量	E_{AS}	36	mJ
Thermal Resistance Junction-C/A 热阻	$R_{\theta JC}/R_{\theta JA}$	2.2/30	$^\circ\text{C}/\text{W}$
Junction/Storage Temperature 结温/储存温度	T_J, T_{stg}	-55~150	$^\circ\text{C}$

■ Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Typ 典型值	Max 最大值	Unit 单位
Drain-Source Breakdown Voltage 漏极-源极击穿电压($I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$)	BV_{DSS}	100	—	—	V
Gate Threshold Voltage 栅极开启电压($I_D=250\mu\text{A}$, $V_{GS}=V_{DS}$)	$V_{GS(th)}$	1.2	1.9	2.3	V
Zero Gate Voltage Drain Current 零栅压漏极电流($V_{GS}=0\text{V}$, $V_{DS}=100\text{V}$)	I_{DSS}	—	—	1	μA
Gate Body Leakage 栅极漏电流($V_{GS}=\pm 20\text{V}$, $V_{DS}=0\text{V}$)	I_{GSS}	—	—	± 100	nA
Static Drain-Source On-State Resistance 静态漏源导通电阻($I_D=20\text{A}$, $V_{GS}=10\text{V}$) ($I_D=16\text{A}$, $V_{GS}=4.5\text{V}$)	$R_{DS(ON)}$	—	6.8 8.5	8.5 10	$\text{m}\Omega$
Diode Forward Voltage Drop 内附二极管正向压降($I_{SD}=20\text{A}$, $V_{GS}=0\text{V}$)	V_{SD}	—	0.85	1.2	V
Input Capacitance 输入电容 ($V_{GS}=0\text{V}$, $V_{DS}=50\text{V}$, $f=1\text{MHz}$)	C_{ISS}	—	2455	—	pF
Common Source Output Capacitance 共源输出电容($V_{GS}=0\text{V}$, $V_{DS}=50\text{V}$, $f=1\text{MHz}$)	C_{OSS}	—	150	—	pF
Reverse Transfer Capacitance 反馈电容 ($V_{GS}=0\text{V}$, $V_{DS}=50\text{V}$, $f=1\text{MHz}$)	C_{RSS}	—	15	—	pF
Total Gate Charge 栅极电荷密度 ($V_{DS}=50\text{V}$, $I_D=20\text{A}$, $V_{GS}=10\text{V}$)	Q_g	—	45	—	nC
Gate Source Charge 栅源电荷密度 ($V_{DS}=50\text{V}$, $I_D=20\text{A}$, $V_{GS}=10\text{V}$)	Q_{gs}	—	8	—	nC
Gate Drain Charge 栅漏电荷密度 ($V_{DS}=50\text{V}$, $I_D=20\text{A}$, $V_{GS}=10\text{V}$)	Q_{gd}	—	12	—	nC
Turn-ON Delay Time 开启延迟时间 ($V_{DS}=50\text{V}$, $I_D=20\text{A}$, $R_{GEN}=3\Omega$, $V_{GS}=10\text{V}$)	$t_{d(on)}$	—	8	—	ns
Turn-ON Rise Time 开启上升时间 ($V_{DS}=50\text{V}$, $I_D=20\text{A}$, $R_{GEN}=3\Omega$, $V_{GS}=10\text{V}$)	t_r	—	13	—	ns
Turn-OFF Delay Time 关断延迟时间 ($V_{DS}=50\text{V}$, $I_D=20\text{A}$, $R_{GEN}=3\Omega$, $V_{GS}=10\text{V}$)	$t_{d(off)}$	—	25	—	ns
Turn-OFF Fall Time 关断下降时间 ($V_{DS}=50\text{V}$, $I_D=20\text{A}$, $R_{GEN}=3\Omega$, $V_{GS}=10\text{V}$)	t_f	—	9	—	ns

■ Typical Characteristic Curve 典型特性曲线

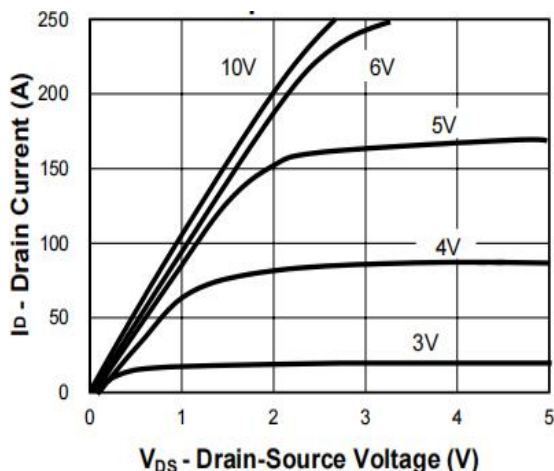


Figure 1: Output Characteristics

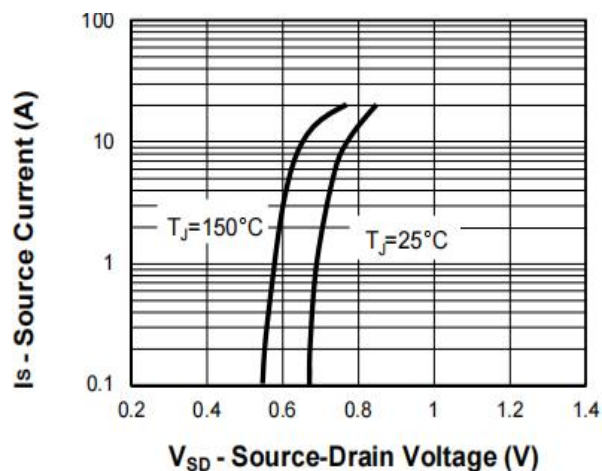


Figure 2: Diode Forward Characteristics

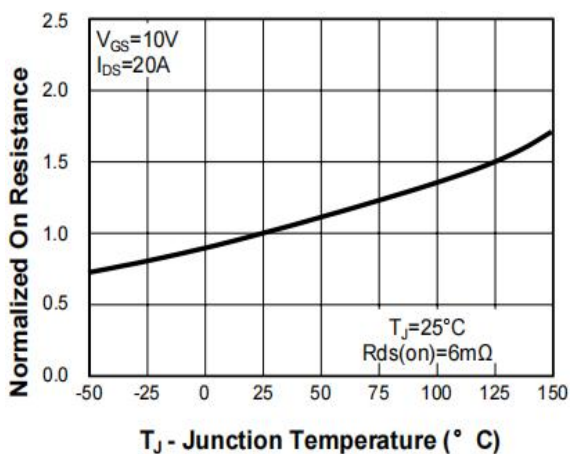


Figure 3: On-Resistance vs. T_J

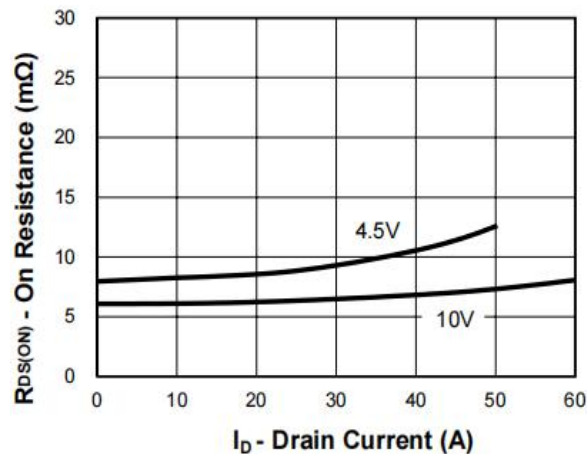


Figure 4: On-Resistance vs. Drain Current

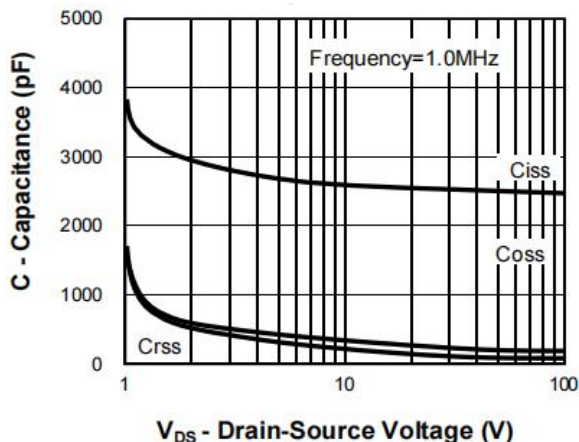


Figure 5: Capacitance Characteristics

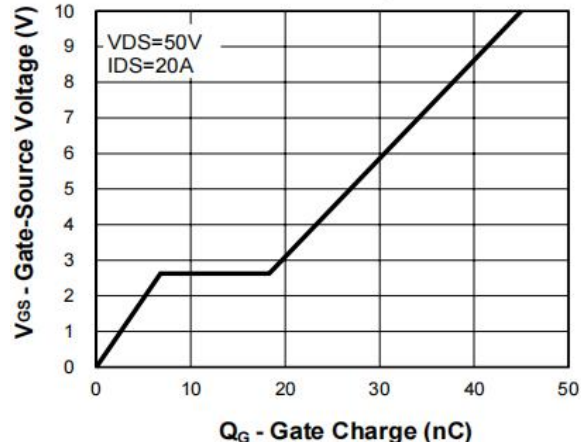


Figure 6: Gate-Charge Characteristics

■ Typical Characteristic Curve 典型特性曲线

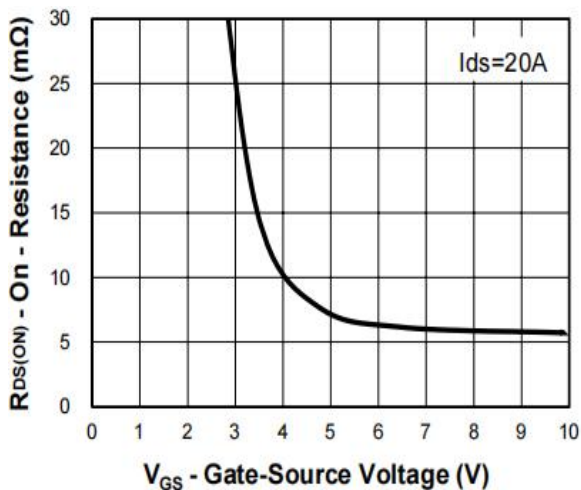


Figure 7: Drain Current vs. V_{GS}

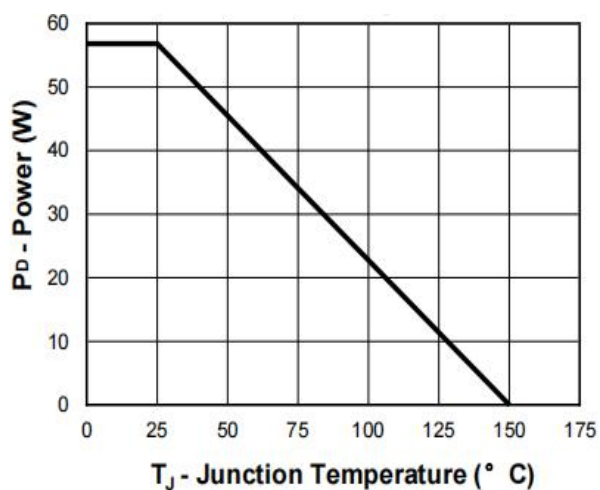


Figure 8: Power Rating Curve

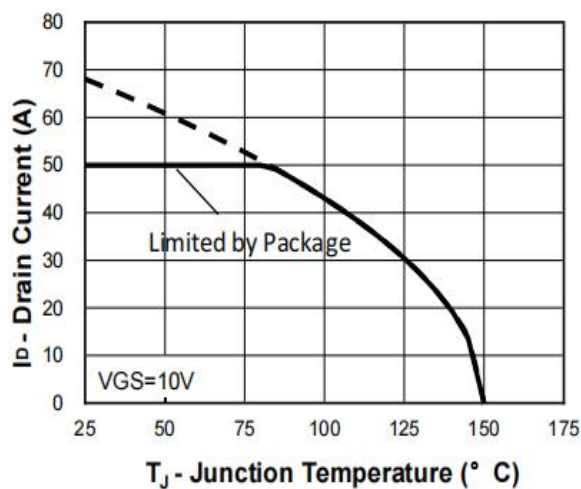


Figure 9: Drain Current Characteristics

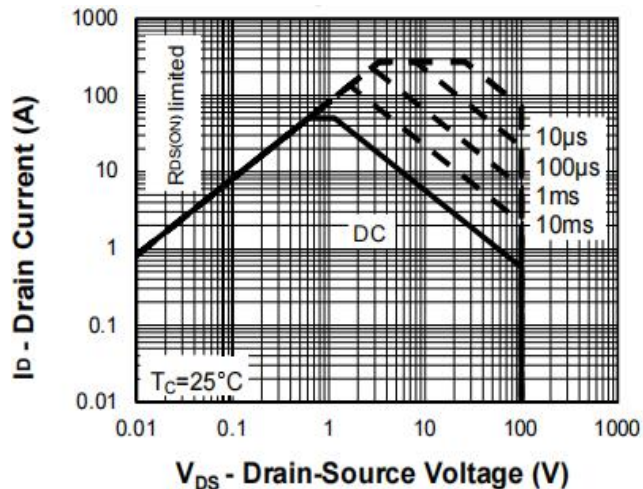


Figure 10: Safe Operating Area

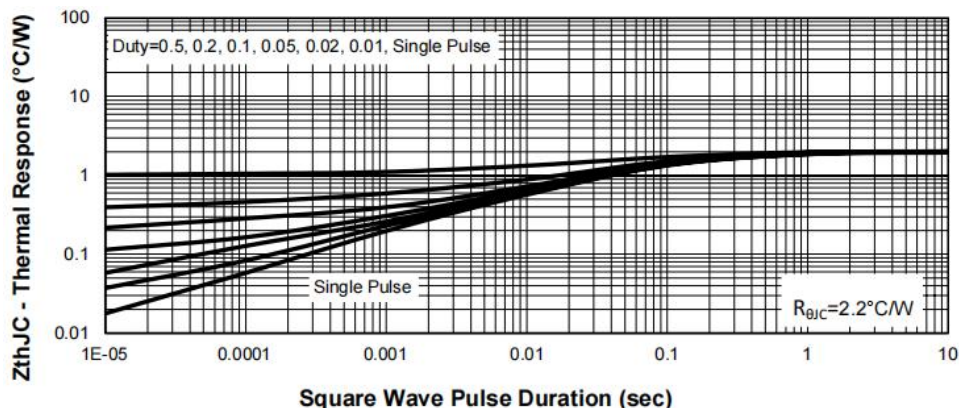
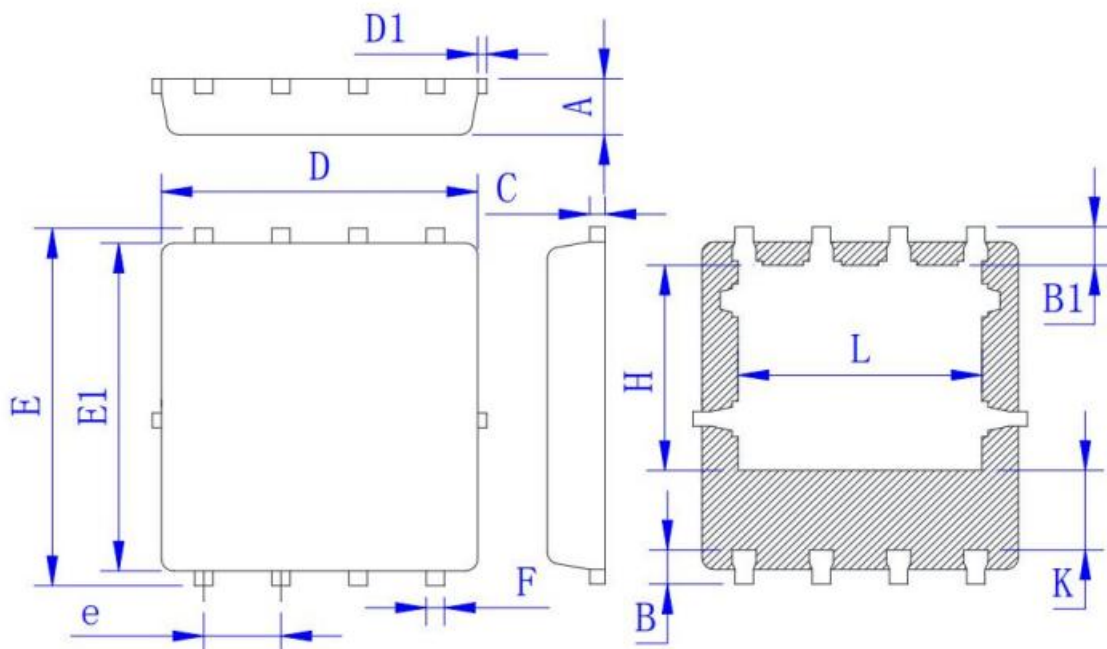


Figure 11: Transient Thermal Response Curve

■ Dimension 外形封装尺寸



Symbol	Min	Typ	Max
A	0.90	0.95	1.00
B	0.48	0.58	0.68
B1	0.55	0.65	0.75
C	0.20	0.254	0.30
D	5.10	5.20	5.30
D1			0.15
E	5.90	6.05	6.20
E1	5.40	5.55	5.70
e	1.22	1.27	1.32
F	0.25	0.30	0.35
H	3.27	3.47	3.67
L	3.80	4.00	4.20
K	1.20		

UNIT 单位: mm 毫米